Mohammed Zeghouane

List of Publications by Year
in descending order

12	73	1683354 5	1473754 9
papers	citations	h-index	g-index

12	12	12	111
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Growth of Ge_{1â”’x}Sn_x Nanowires by Chemical Vapor Deposition via Vaporâ€“Liquidâ€“Solid Mechanism Using GeH₄ and SnCl₄. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700743.	0.8	18
2	Selective growth of ordered hexagonal InN nanorods. CrystEngComm, 2019, 21, 2702-2708.	1.3	13
3	Compositional control of homogeneous InGaN nanowires with the In content up to 90%. Nanotechnology, 2019, 30, 044001.	1.3	12
4	Crystal engineering by tuning the growth kinetics of GaN 3-D microstructures in SAG-HVPE. CrystEngComm, 2018, 20, 6207-6213.	1.3	6
5	Impact of droplet composition on the nucleation rate and morphology of vapor-liquid-solid GeSn nanowires. Nanotechnology, 2020, 31, 405602.	1.3	5
6	Formation of voids in selective area growth of InN nanorods in SiN_x on GaN templates. Nano Futures, 2020, 4, 025002.	1.0	5
7	Morphological Control of InN Nanorods by Selective Area Growthâ€“Hydride Vapor-Phase Epitaxy. Crystal Growth and Design, 2020, 20, 2232-2239.	1.4	5
8	Selective Area Growth by Hydride Vapor Phase Epitaxy and Optical Properties of InAs Nanowire Arrays. Crystal Growth and Design, 2021, 21, 5158-5163.	1.4	5
9	Long catalyst-free InAs nanowires grown on silicon by HVPE. CrystEngComm, 2021, 23, 378-384.	1.3	4
10	Thermodynamics of the Vaporâ€“Liquidâ€“Solid Growth of Ternary IIIâ€“V Nanowires in the Presence of Silicon. Nanomaterials, 2021, 11, 83.	1.9	0
11	Comprehensive model toward optimization of SAG In-rich InGaN nanorods by hydride vapor phase epitaxy. Nanotechnology, 2021, 32, 155601.	1.3	0
12	Enhancing the incorporation of Sn in vaporâ€“liquidâ€“solid GeSn nanowires by modulation of the droplet composition. Nanotechnology, 2022, 33, 245605.	1.3	0